SEARCH REQUEST FORM Scientific and Technical Information Center - EIC2800 Rev. 3/15/2004 This is an experimental format Please give suggestions or comments to Jeff Harrison, JEF-4B68, 272-2511.
Date 430/04 Serial # 10/634/917 Priority Application Date 5/16/03
Your Name Examiner #
AU 2829 Phone 292-1838 Room 5430
In what format would you like your results? Paper is the default. PAPER DISK EMAIL
If submitting more than one search, please prioritize in order of need.
The EIC searcher normally will contact you before beginning a prior art search. If you would like to sit with a searcher for an interactive search, please notify one of the searchers.
Where have you searched so far on this case? Circle: USPT DWPI EPO Abs JPO Abs IBM TDB
Other:
What relevant art have you found so far? Please attach pertinent citations or Information Disclosure Statements. 115 6555857
What types of references would you like? Please checkmark: Primary Refs Nonpatent Literature Other Secondary Refs Foreign Patents
Teaching Refs
desired focus of this search? Please include the concepts, synonyms, keywords, acronyms, registry numbers, definitions, structures, strategies, and anything else that helps to describe the topic. Please attach a copy of the abstract and pertinent claims.
troblem! De e Pare 1-3
Solution' 1544
FIRST pass of search should be
- Power Semiconductor Device
- Beffer on lesistance
- Better Breakdown Voltage
- GaN /AlGaN
_ 3 + Semicond layers
Staff Use Only Type of Search Vendors
Searcher: HARRISCA Structure (#) STN X
Searcher Phone: 22511 Bibliographic Dialog &
Searcher Location: STIC-EIC2800, JEF-4B68 Litigation Questel/Orbit
Date Completed: 7-20-04 Patent Family WWW/Internet_
Searcher Prep/Rev Time: 35 + 50 Other Other Other

```
FILE 'HCAPLUS' ENTERED AT 12:23:52 ON 20 JUL 2004
                E POWER SEMI/CT
                E E4+ALL/CT
          13114 SEA ABB=ON PLU=ON "SEMICONDUCTOR DEVICES (L) POWER"/CT OR
L1
                 "POWER TRANSISTORS"/CT OR (TRANSISTOR OR FIELD EFFECT OR FET
                OR SEMICONDUCT####### (3A) (POWER OR SWITCH####) OR SWITCH#### (2A)
                ) POWER###
          13981 SEA ABB=ON PLU=ON POWER DEVICE OR L1
L2
                E NITRIDE SEMICON/CT
                S L2 AND (E6 OR NITRIDE SEMICONDUCT###### OR GAN OR ALGAN OR AL
     FILE 'REGISTRY' ENTERED AT 12:28:11 ON 20 JUL 2004
             17 SEA ABB=ON PLU=ON GA.N/MF
L3
     FILE 'HCAPLUS' ENTERED AT 12:28:11 ON 20 JUL 2004
             15 SEA ABB=ON PLU=ON L3
L4
     FILE 'REGISTRY' ENTERED AT 12:28:12 ON 20 JUL 2004
            187 SEA ABB=ON PLU=ON AL.GA.N/MF
L5
     FILE 'HCAPLUS' ENTERED AT 12:28:12 ON 20 JUL 2004
           6733 SEA ABB=ON PLU=ON L5
L6
            365 SEA ABB=ON PLU=ON L2 AND (NITRIDES/CT OR NITRIDE SEMICONDUCT#
L7
                 ##### OR GAN OR ALGAN OR L6 OR L4 OR GALLIUM NITRIDE)
     FILE 'REGISTRY' ENTERED AT 12:29:09 ON 20 JUL 2004
               1 SEA ABB=ON PLU=ON DIAMOND/CN
L8
            1097 SEA ABB=ON PLU=ON (C.SI/MF OR C SI/ELF) AND CARBIDE
L9
                 D IDE L8
     FILE 'HCAPLUS' ENTERED AT 12:30:28 ON 20 JUL 2004
            116 SEA ABB=ON PLU=ON L2 AND L8
L10
             678 SEA ABB=ON PLU=ON L2 AND L9
L11
             144 SEA ABB=ON PLU=ON L2 AND INTRINSIC
L12
             129 SEA ABB=ON PLU=ON L2 AND (WIDE## BANDGAP OR WIDE## BAND GAP)
1.13
      FILE 'HCAPLUS' ENTERED AT 12:31:33 ON 20 JUL 2004
      FILE 'HCAPLUS' ENTERED AT 12:31:44 ON 20 JUL 2004
               4 SEA ABB=ON PLU=ON L2 AND ((VARY### OR VARI#####)(2A)(BANDGAP
L14
                 OR BAND GAP))
             778 SEA ABB=ON PLU=ON L2 AND (STACK####### OR SANDWICH##### OR
1.15
                 LAMINA###### OR MULTIL? OR (MULTI OR MULTIPLE OR THREE OR FOUR
                 OR FIVE OR SIX OR SIXTH OR FIFTH OR FOURTH OR THIRD) (1W) (LAYER#
                 ### OR LEVEL###))
            2314 SEA ABB=ON PLU=ON L2 AND (ELECTRODE OR ANODE OR CATHODE OR
T.16
                 PLATE)
              73 SEA ABB=ON PLU=ON L2 AND ELECTRODE(2A)CONTROL######
288 SEA ABB=ON PLU=ON L2 AND CONTROL######
L17
            2288 SEA ABB=ON
T.18
                             PLU=ON L15 AND L16
             226 SEA ABB=ON
1.19
               2 SEA ABB=ON PLU=ON L15 AND L17
L20
             126 SEA ABB=ON PLU=ON L15 AND L18
L21
              36 SEA ABB=ON PLU=ON L19 AND L21
L22
      FILE 'REGISTRY' ENTERED AT 12:36:22 ON 20 JUL 2004
             460 SEA ABB=ON PLU=ON GALLIUM NITRIDE
L23
      FILE 'HCAPLUS' ENTERED AT 12:36:39 ON 20 JUL 2004
             297 SEA ABB=ON PLU=ON L2 AND L23
182 SEA ABB=ON PLU=ON L2 AND (L3 OR L4 OR L5)
1199 SEA ABB=ON PLU=ON (L7 OR (L10 OR L11 OR L12 OR L13) OR L14
L24
L25
            1199 SEA ABB=ON
L26
                 OR L25)
```

1203 SEA ABB=ON PLU=ON (L7 OR (L10 OR L11 OR L12 OR L13) OR L14

L27

			OR L25 OR L24)
L28		316	SEA ABB=ON PLU=ON L15 AND (L16 OR L17 OR L18)
L29		22	SEA ABB=ON PLU=ON L27 AND L28
	DEL	32	S L27 AND SCHOTTKY AND (JUNCTION#### OR HETEROJUBCT?)
L30		40	SEA ABB=ON PLU=ON L27 AND SCHOTTKY AND (JUNCTION#### OR HETEROJUNCT?)
L31		23	SEA ABB=ON PLU=ON L15 AND (L29 OR L30)
L32		29	SEA ABB=ON PLU=ON L14 OR L20 OR L31
L33		21	SEA ABB=ON PLU=ON (L2 AND (FOURTH OR FIFTH OR FOUR OR FIVE) (W) (SEMICOND######## OR LAYER######))
L34		48	SEA ABB=ON PLU=ON (L32 OR L33)
L35		12	SEA ABB=ON PLU=ON L34 AND (ELECTRODES OR SEPARAT######(3A) (ELE
			CTRODE OR ANODE OR CATHODE) OR CONTROL####(3A)(FILM OR LAYER#### OR CONDUCT### OR ANODE OR CATHODE))
L36		1	SEA ABB=ON PLU=ON L34 AND PLATE
L37		14	SEA ABB=ON PLU=ON L34 AND (ONRESIST####### OR RESISTANCE#####
			## OR RESISTIV####### OR BREAK###### OR BROKEN)
L38		34	SEA ABB=ON PLU=ON L34 AND (CONCENTRATION OR WT OR WEIGHT OR
			DENSITY OR THICKNESS OR DISTANCE OR GAP OR DOP##### OR
			IMPURIT### OR IMPLANT##### OR N TYPE OR PTYPE OR CONDUCTIVITY)
L39		48	SEA ABB=ON PLU=ON L14 OR L20 OR L29 OR (L31 OR L32 OR L33 OR
			L34 OR L35 OR L36 OR L37 OR L38)
L40		20	SEA ABB=ON PLU=ON L39 AND (PASSIVAT####### OR INSULAT########
			OR DIELEC###### OR SURFACE) D BIB AB HITSTR TOT
- 41		21	SEA ABB=ON PLU=ON L39 AND CONTROL########
L41		21	SEA ABB=ON PLU=ON L14 OR L20 OR L36 OR L41
L42 L43			SEA ABB=ON PLU=ON L42 NOT L40
143		13	D BIB AB HITSTR TOT
L44		15	SEA ABB=ON PLU=ON L8 AND L15
L45		14	SEA ABB=ON PLU=ON L44 NOT (L42 OR L40)
D40			D BIB AB HITSTR TOT
L46		45	SEA ABB=ON PLU=ON (L5 OR L23 OR L9) AND L2 AND (L15 OR
			(FOURTH OR FIFTH OR FOUR OR FIVE) (W) (SEMICOND####### OR
			LAYER#####))
L47		30	SEA ABB=ON PLU=ON L46 NOT (L45 OR L42 OR L40)
L48		12	SEA ABB=ON PLU=ON L47 AND (PASSIVAT####### OR INSULAT########
	٠,		# OR SCHOTTKY OR JUNCTION###### OR HORIZONTAL OR HETEROJUNCTION
			######)
			D ALL HITSTR TOT
L49		25	SEA ABB=ON PLU=ON ((L10 OR L11 OR L12 OR L13) OR L17 OR L22 OR (L24 OR L25) OR (L28 OR L29 OR L30 OR L31 OR L32 OR L33 OR
			L34 OR L35 OR L36 OR L37 OR L38 OR L39 OR L40 OR L41 OR L42 OR
			L43 OR L44 OR L45 OR L46 OR L47 OR L48)) AND SEMICONDUCT#######
			(3A) POWER AND POWER (3A) SWITCH###### AND SEMICONDUCT###### (3A) SW
			ITCH#####
L50		. 61	SEA ABB=ON PLU=ON L48 OR (L45 OR L42 OR L40)
L51			SEA ABB=ON PLU=ON L49 NOT L50
L52			SEA ABB=ON PLU=ON L51 AND (SECOND ELECTRODE OR CATHODE (4A) ANO
202		•	DE OR CONTROL#### (1W) ELECTRODE OR (CATHODE OR ANODE OR
			FLECTRODE OR CONDUCT####) (3A) PLATE)
L53		16	SEA ABB=ON PLU=ON ((L8 OR L9) OR L23 OR INTRINSIC OR
			NITRIDES/IT(L)SEMICONDUCT####### OR BANDGAP OR BAND GAP) AND
			L51
L54			SEA ABB=ON PLU=ON L51 AND (L52 OR L53)
L55			SEA ABBEON PLUEON L54 AND SECOND ELECTRODE
L56		3	SEA ABBEON PLUEON L54 AND (FOURTH OR FIFTH OR THIRD OR THREE
			OR FIVE OR FOUR)
			D ALL HITSTR TOT
L57			SEA ABB=ON PLU=ON L54 NOT L56 SEA ABB=ON PLU=ON L57 AND 2002/PY
L58			V-10 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1
L59		6	
			D ALL HITSTR TOT E ELECTRODES/CT
L60		1	SEA ABB=ON PLU=ON L57 AND ELECTRODES+NT/CT
POA		т	CONTROL ON THE ON THE PERSON OF

D ALL HITSTR

2 SEA ABB=ON PLU=ON L57 AND (?CONNECT?) D ALL HITSTR TOT

FILE 'SCISEARCH' ENTERED AT 13:06:02 ON 20 JUL 2004

E ZHANG N Q, 2000/RE

L61

L62

52 SEA ABB=ON PLU=ON ("ZHANG N Q, 1999, P212, INT C SOL STAT DEV M"/RE OR "ZHANG N Q, 1999, V22, P221, COMPUT ELECTRON AGR"/RE OR "ZHANG N Q, 2000"/RE OR "ZHANG N Q, 2000, V21, IEEE ELECT DEVICE LE"/RE OR "ZHANG N Q, 2000, V21, P373, IEEE ELECT DEVICE LE"/RE OR "ZHANG N Q, 2000, V21, P373, IEEE ELECTR DEVICE L"/RE OR "ZHANG N Q, 2000, V21, P421, IEEE ELECTR
DEVICE L"/RE OR "ZHANG N Q, 2001, 4 INT C NITR SEM DEN"/RE OR "ZHANG N Q, 2001, IEDM TECH DIG"/RE OR "ZHANG N Q, 2001, P589, IEDM"/RE OR "ZHANG N Q, 2001, P589, IEDM TECH DIG"/RE OR "ZHANG N Q, 2001, V188, P213, PHYS STATUS SOLIDI A"/RE)
7 SEA ABB=ON PLU=ON KARMALKAR S, 2001?/RE

L63

55 SEA ABB=ON PLU=ON (L62 OR L63) L64

26 SEA ABB=ON PLU=ON L64 AND PY<2003

L65 5 SEA ABB=ON PLU=ON L65 AND (STACK####### OR SANDWICH##### OR L66 MULTIL###### OR MULTIPLE OR MULTI OR SEVERAL OR THIRD OR FOURTH OR FIFTH OR THREE OR FOUR OR FIVE) D ALL TOT

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FILE 'WPIX, EUROPATFULL, PCTFULL' ENTERED AT 14:55:33 ON 20 JUL 2004
          61952 SEA ABB=ON PLU=ON FIELD PLATE OR FIELD ELECTRODE OR PLATE##(2
L1
               A) (ELECTRODE OR CONDUCT###)
          27873 SEA ABB=ON PLU=ON CONTROL##(2W)(ELECTRODE OR CONDUCT###)
L2
          15256 SEA ABB=ON PLU=ON THIRD(W) LAYER OR THIRD(W) SEMICONDUCT####(
L3
               W) LAYER
          46816 SEA ABB=ON PLU=ON SEPARATE##(2A) ELECTRODE OR SECOND(W)
L4
               ELECTRODE OR MAIN ELECTRODES OR PRIMARY ELECTRODES
             96 SEA ABB=ON PLU=ON L2 AND L3 AND L4
L5
            13 SEA ABB=ON PLU=ON L1 AND L5
L6
          75146 SEA ABB=ON PLU=ON N TYPE OR P TYPE OR CONDUCTIVITY TYPE OR
L7
                FIRST CONDUCTIVITY
             57 SEA ABB=ON PLU=ON L5 AND L7
L8
                                   (BETWEEN OR SEPARAT###) (3A) (CONTROL#### OR
        331756 SEA ABB=ON PLU=ON
L9
               ELECTRODE)
             48 SEA ABB=ON PLU=ON L8 AND L9
L10
            947 SEA ABB=ON PLU=ON SECOND PRIMARY ELECTRODE OR SECOND MAIN
L11
               ELECTRODE
             11 SEA ABB=ON PLU=ON L10 AND L11
L12
                                   L6 AND (L7 OR L8 OR L9 OR L10 OR L11)
             12 SEA ABB=ON PLU=ON
L13
                                   (L12 OR L13) AND (FOURTH OR FIFTH) (W) (SEMIC
             16 SEA ABB=ON PLU=ON
L14
                ONDUCT### OR LAYER)
                                   (L12 OR L13 OR L14) AND (POWER OR SWITCH###
              6 SEA ABB=ON PLU=ON
L15
                )/TI,AB,CE
                D TI 1-6
                D BIB AB KWIC 1-6
             24 SEA ABB=ON PLU=ON L6 OR (L12 OR L13 OR L14 OR L15)
L16
                D TI 1-24
                D MAX 1
              5 SEA ABB=ON PLU=ON (L5 OR L8 OR L10) AND POWER/TI AND
L17
                (SWITCH### OR DEVICE)/TI
                D TI 1-5
                D MAX 1-2
                D BIB AB KWIC 3-5
```

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CAS/STN FILE 'HCAPLUS' ENTERED AT 12:23:52 ON 20 JUL 2004
                E POWER SEMI/CT
          13114
                         "SEMICONDUCTOR DEVICES (L) POWER"/CT OR "POWER TRANSISTORS"/CT OR (TRANSISTOR OR FIELD
                    S
Ll
EFFECT OR FET OR SEMICONDUCT#######) (3A) (POWER OR SWITCH####) OR SWITCH#### (2A) POWER###
                         POWER DEVICE OR L1
                    S
L2
          13981
                S L2 AND (E6 OR NITRIDE SEMICONDUCT###### OR GAN OR ALGAN OR AL
     FILE 'REGISTRY' ENTERED AT 12:28:11 ON 20 JUL 2004
                    S
                         GA.N/MF
L3
     FILE 'HCAPLUS' ENTERED AT 12:28:11 ON 20 JUL 2004
             15
                    S
                         L3
L4
     FILE 'REGISTRY' ENTERED AT 12:28:12 ON 20 JUL 2004
                         AL.GA.N/MF
L5
            187
                    S
     FILE 'HCAPLUS' ENTERED AT 12:28:12 ON 20 JUL 2004
           6733
                    s
                         L5
L6
                         L2 AND (NITRIDES/CT OR NITRIDE SEMICONDUCT###### OR GAN OR ALGAN OR L6 OR L4 OR GALLIUM
            365
                    s
1.7
NITRIDE)
     FILE 'REGISTRY' ENTERED AT 12:29:09 ON 20 JUL 2004
                         DIAMOND/CN
L8
                    S
              1
                          (C.SI/MF OR C SI/ELF) AND CARBIDE
Ь9
           1097
                    S
     FILE 'HCAPLUS' ENTERED AT 12:30:28 ON 20 JUL 2004
                    S
                         L2 AND L8
L10
            116
                         L2 AND L9
            678
                    s
T.11
                         L2 AND INTRINSIC
L12
            144
                    S
                         L2 AND (WIDE## BANDGAP OR WIDE## BAND GAP)
            129
                    s
L13
                         L2 AND ((VARY### OR VARI#####)(2A)(BANDGAP OR BAND GAP))
L14
              4
                    9
                         L2 AND (STACK####### OR SANDWICH##### OR LAMINA###### OR MULTIL? OR (MULTI OR MULTIPLE
            778
                    S
L15
OR THREE OR FOUR OR FIVE OR SIX OR SIXTH OR FIFTH OR FOURTH OR THIRD) (1W) (LAYER#### OR LEVEL###))
                         L2 AND (ELECTRODE OR ANODE OR CATHODE OR PLATE)
L16
           2314
                    S
                         L2 AND ELECTRODE (2A) CONTROL######
             73
                    s
L17
                          L2 AND CONTROL######
L18
           2288
                     s
            226
                     s
                         L15 AND L16
T.19
                         L15 AND L17
L20
              2
                     s
L21
            126
                    S
                          L15 AND L18
                          L19 AND L21
L22
             36
                     s
     FILE 'REGISTRY' ENTERED
L23
            460
                    s
                         GALLIUM NITRIDE
     FILE 'HCAPLUS' ENTERED
L24
            297
                    S
                          L2 AND L23
                          L2 AND (L3 OR L4 OR L5)
            182
L25
                     S
                          (L7 OR (L10 OR L11 OR L12 OR L13) OR L14 OR L25)
L26
           1199
                          (L7 OR (L10 OR L11 OR L12 OR L13) OR L14 OR L25 OR L24)
           1203
                     s
L27
            316
                     Ş
                          L15 AND (L16 OR L17 OR L18)
L28
             22
                     S
                          L27 AND L28
1.29
                          L27 AND SCHOTTKY AND (JUNCTION#### OR HETEROJUNCT?)
             40
                     S
L30
                          L15 AND (L29 OR L30)
L31
             23
                     S
                          L14 OR L20 OR L31
L32
             29
                     S
                          (L2 AND (FOURTH OR FIFTH OR FOUR OR FIVE) (W) (SEMICOND######## OR LAYER######))
L33
             21
                     S
             48
                     s
                          (L32 OR L33)
L34
                          L34 AND (ELECTRODES OR SEPARAT######(3A) (ELECTRODE OR ANODE OR CATHODE) OR
L35
             12
                     S
CONTROL#### (3A) (FILM OR LAYER#### OR CONDUCT### OR ANODE OR CATHODE))
                          L34 AND PLATE
L36
              1
                     S
                          L34 AND (ONRESIST####### OR RESISTANCE####### OR RESISTIV####### OR BREAK###### OR
L37
             14
                     s
BROKEN)
                          L34 AND (CONCENTRATION OR WT OR WEIGHT OR DENSITY OR THICKNESS OR DISTANCE OR GAP OR
L38
              34
DOP##### OR IMPURIT### OR IMPLANT##### OR N TYPE OR PTYPE OR CONDUCTIVITY)
                          L14 OR L20 OR L29 OR (L31 OR L32 OR L33 OR L34 OR L35 OR L36 OR L37 OR L38)
L39
              48
                     S
                          L39 AND (PASSIVAT####### OR INSULAT####### OR DIELEC###### OR SURFACE)
             20
                     S
T.40
                          L39 AND CONTROL#######
L41
             21
                     S
                          L14 OR L20 OR L36 OR L41
              26
                     s
L42
                          L42 NOT L40
L43
             15
                     S
                          L8 AND L15
L44
             15
                     S
                     S
                          1.44 NOT (L42 OR L40)
L45
             14
                          (L5 OR L23 OR L9) AND L2 AND (L15 OR (FOURTH OR FIFTH OR FOUR OR
1.46
              45
                     S
FIVE) (W) (SEMICOND#######
                         # OR LAYER####))
```

L46 NOT (L45 OR L42 OR L40)

. ,

L47

30

S

FILE 'HCAPLUS' ENTERED 12 S L47 AND (PASSIVAT####### OR INSULAT######## OR SCHOTTKY OR JUNCTION###### OR L48 HORIZONTAL OR HETEROJUNCTION######) ((L10 OR L11 OR L12 OR L13) OR L17 OR L22 OR (L24 OR L25) OR (L28 OR L29 OR L30 OR L31 L49 25 S OR L32 OR L33 OR L34 OR L35 OR L36 OR L37 OR L38 OR L39 OR L40 OR L41 OR L42 OR L43 OR L44 OR L45 OR L46 OR L47 OR L48)) AND SEMICONDUCT######## (3A) POWER AND POWER(3A) SWITCH##### AND SEMICONDUCT###### (3A) SWITCH###### L48 OR (L45 OR L42 OR L40) L50 61 S 23 S L49 NOT L50 L51 L51 AND (SECOND ELECTRODE OR CATHODE (4A) ANODE OR CONTROL####(1W) ELECTRODE OR (CATHODE L52 6 S OR ANODE OR ELECTRODE OR CONDUCT####) (3A) PLATE) ((L8 OR L9) OR L23 OR INTRINSIC OR 16 S L53 NITRIDES/IT(L)SEMICONDUCT####### OR BANDGAP OR BAND GAP) AND L51 21 L51 AND (L52 OR L53) S L54 L54 AND SECOND ELECTRODE L55 0 S L56 3 S L54 AND (FOURTH OR FIFTH OR THIRD OR THREE OR FIVE OR FOUR) L54 NOT L56 L57 18 S L57 AND 2002/PY L58 6 L58 NOT L56 L59 6 S

FILE 'SCISEARCH' ENTERED

s

S

1

2

L60

L61

L57 AND ELECTRODES+NT/CT

L57 AND (?CONNECT?)

	FILL	2022		
		E	ZHAN	IG N Q, 2000/RE
L62		52	s	(ZHANG N Q, 2000"/RE OR "ZHANG N Q, 2000, V21, IEEE ELECT DEVICE LE"/RE OR)
L63		7	s	KARMALKAR S, 2001?/RE
L64		55	s	(L62 OR L63)
L65		26	s	L64 AND PY<2003
L66		5	s	L65 AND (STACK####### OR SANDWICH##### OR MULTIL###### OR MULTIPLE OR MULTI OR SEVERAL
OR T	HIRD O	R FOURTH	OR	FIFTH OR THREE OR FOUR OR FIVE)

20jul04 08:54:13 User259284 Session D2847.2

File 2:INSPEC 1969-2004/Jul W2 (c) 2004 Institution of Electrical Engineers

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Set
       Items
               Description
               POWER????(5N) SEMICOND?????? AND POWER????(5N) SWITCH????? A-
         3863
S1
            ND SWITCH?????(5N)SEMICOND????????
              S1 AND (STACK? OR SANDWICH? OR MULTIL? OR (MULTIPLE OR MUL-
            TI OR THREE OR FOUR OR FIVE) (2W) (LAYER????? OR FILM OR FILMS))
               S2 AND ON()RESISTANCE??
S3
               S2 AND ON()RESISTIVIT???
            0
S4
        39096
               R1:R4 OR R6 OR R8:R17
S5
               S5 AND (STACK? OR SANDWICH? OR MULTIL? OR (MULTIPLE OR MUL-
S6
            TI OR THREE OR FOUR OR FIVE) (2W) (LAYER????? OR FILM OR FILMS))
          906
               S2 OR S6
S7
S8
        39258
               S1 OR S5
S9
          18
               S7 AND SCHOTTKY
S10
          980
               S8 AND SCHOTTKY
               S7:S8 AND (RESISTANCE?? OR RESISTIV?????? OR ONRESIST?) AND
          933
S11
              (AVALANCH? OR BREAKDOWN? OR BREAK????? OR BROKE????)
          408
               (S2 OR S6:S7 OR S9:S11) AND (DIAMOND OR SIC OR GAN OR ALGAN
S12
             OR NITRIDE() SEMICONDUCT????? OR CI=SIC OR CI=CSI OR CI=GAN OR
              CI=ALGAN OR CI=(AL SS(S)GA SS(S)N SS))
S13
           47
                (S2 OR S6:S7 OR S9:S11) AND CI=(GA SS(S)N SS)(S)NE=2
                (S2 OR S6:S7 OR S9:S11) AND CI=(GA SS(S)N SS)(S)NE=3
S14
           54
                (S2 OR S6:S7 OR S9:S11) AND CI=(GA SS(S)N SS)(S)NE=4
S15
           1
                (S2 OR S6:S7 OR S9:S11) AND CI=(GA BIN(S)N BIN)(S)NE=4
S16
           8
                (S2 OR S6:S7 OR S9:S11) AND CI=(GA BIN(S)N BIN)(S)NE=3
           50
S17
                (S2 OR S6:S7 OR S9:S11) AND CI=(GA BIN(S)N BIN)(S)NE=2
           91
S18
           91
                (S2 OR S6:S7 OR S9:S11) AND CI=(GA BIN(S)N BIN)
S19
S20
          410
               S12:S19
                S20 AND (S2 OR S6)
S21
                S21 AND (PASSIVAT?????? OR INSULAT?????? OR DIELEC???????)
S22
                S21 AND (PLATE OR PLATES OR ANODE? ? OR CATHODE? ? OR ELEC-
S23
            TRODE? ? OR CONTROL?????(2N) (ELECTRODE? ?))
                S15:S16 OR S22:S23
           15
S24
           15
                S24 NOT S3
$25
S26
          .10
                S25 AND (WIDE?? OR BANDGAP? OR BAND()GAP??? OR EV OR IMPUR-
             IT?????? OR DOP??????? OR IMPLANT????? OR CI=DOP)
S27
                $25 AND POWER AND SWITCH???????
                S27 NOT S26
S28
            2
                S28 NOT S3
S29
            2
                S25 AND SEMICOND???????(4N) (POWER???? OR SWITCH?????)
S30
            9
                S30 NOT (S3 OR S27 OR S26)
            1
$31
S32
            2
                S25 NOT (S27 OR S26 OR S31)
                S32 NOT S3
S33
S34
                S25 NOT (S29 OR S26 OR S31)
                S34 NOT S3
S35
           2
```

	FILE 'WPIX,	, EUROPATFULL, PCTFULL' ENTERED AT 14:55:33 ON 20 JUL 2004
L1	61952	SEA ABB=ON PLU=ON FIELD PLATE OR FIELD ELECTRODE OR PLATE##(2
		A) (ELECTRODE OR CONDUCT###)
L2	27873	SEA ABB=ON PLU=ON CONTROL##(2W)(ELECTRODE OR CONDUCT###)
L3	15256	SEA ABB=ON PLU=ON THIRD(W) LAYER OR THIRD(W) SEMICONDUCT####(
		W) LAYER
L4	46816	SEA ABB=ON PLU=ON SEPARATE##(2A) ELECTRODE OR SECOND(W)
		ELECTRODE OR MAIN ELECTRODES OR PRIMARY ELECTRODES
L5	96	SEA ABB=ON PLU=ON L2 AND L3 AND L4
L6	13	SEA ABB=ON PLU=ON L1 AND L5
L7	75146	SEA ABB=ON PLU=ON N TYPE OR P TYPE OR CONDUCTIVITY TYPE OR
		FIRST CONDUCTIVITY
L8	57	SEA ABB=ON PLU=ON L5 AND L7
L9	331756	SEA ABB=ON PLU=ON (BETWEEN OR SEPARAT###) (3A) (CONTROL#### OR
		ELECTRODE)
L10		SEA ABB=ON PLU=ON L8 AND L9
L11	947	SEA ABB=ON PLU=ON SECOND PRIMARY ELECTRODE OR SECOND MAIN
		ELECTRODE
L12	11	SEA ABB=ON PLU=ON L10 AND L11
L13	12	SEA ABB=ON PLU=ON L6 AND (L7 OR L8 OR L9 OR L10 OR L11)
L14	16	SEA ABB=ON PLU=ON (L12 OR L13) AND (FOURTH OR FIFTH) (W) (SEMIC
		ONDUCT### OR LAYER)
L15	6	SEA ABB=ON PLU=ON (L12 OR L13 OR L14) AND (POWER OR SWITCH###
)/TI,AB,CE
		D TI 1-6
		D BIB AB KWIC 1-6
L16	24	SEA ABB=ON PLU=ON L6 OR (L12 OR L13 OR L14 OR L15)
		D TI 1-24
		D MAX 1
L17	5	SEA ABB=ON PLU=ON (L5 OR L8 OR L10) AND POWER/TI AND
		(SWITCH### OR DEVICE)/TI

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SYSTEM:OS - DIALOG OneSearch
File 348:EUROPEAN PATENTS 1978-2004/Jul W02
(c) 2004 European Patent Office
File 349:PCT Fulltext 1979-2002/UB=20040708,UT=20040701
(c) 2004 WIPO/Univentio

Set	Items	Description
S1	388	(FOURTH OR FOUR) (W) (LAYER??? OR SEMICONDUCT????)/TI,AB,CE
S2	183	(FIVE OR FIFTH) (W) (LAYER??? OR SEMICONDUCT????) /TI, AB, CE
s3	58	1AND2
S4	207	(SEMICONDUCT?????(4N) POWER???? AND POWER????(4N) SWITCH?????
	A	ND SEMICONDUCT?????(4N)SWITCH????)/TI,AB,CE
\$5	0	3AND4
S6	1	S1:S2 AND S4
S 7	249	(SEMICONDUCT?????(4N)POWER???? AND POWER????(4N)SWITCH????-
	?)	/TI,AB,CE
S8	232	(SEMICONDUCT?????(4N)POWER???? AND SEMICONDUCT?????(4N)SWI-
	TC	CH????)/TI,AB,CE
S9	289	(POWER????(4N)SWITCH????? AND SEMICONDUCT?????(4N)SWITCH??-
	??	P)/TI,AB,CE
S10	0	S3 AND S7:S9
S11	1	S1:S2 AND S7:S9
S12	0	S11 NOT S6
S13	227	(FIVE OR FIFTH) (2W) (LAYER??? OR SEMICONDUCT????)/TI,AB,CE
S14	6805	(FIVE OR FIFTH) (2W) (LAYER??? OR SEMICONDUCT????)
S15	0	S7:S9 AND S13
S16	5	S7:S9 AND S14
S17	4	S16 NOT S11